## Notice of References Cited

Application/Control No. 10/608,221	Applicant(s)/l Reexamination	on
Examiner	Art Unit	
George Fourson	2823	Page 1 of 1

## **U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-			
	В	US-			
	С	US-			
	D	US-			
	Е	US-			
	F	US-			
	G	US-			
	Ι	US-			
	Т	US-			
	J	US-			
	К	US-			
1	L	US-			
	М	US-			

## FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
17 Table 1	α					
	R					
	S					
	Т					

## **NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Fann-Mei et al, "Formation of Cobalt Silicide Under a Passivating Film of Molybedenum or Tungsten", J.Vac.Sci.Technol. B 9 (3), May/Jun 1991, pp.1497-1502
	V	Alperin, M., et al, "Development of the Self-Aligned Titanium Silicide Process for VLSI Applications", IEEE Transactions on Electron Devices, Vol. ED-32, No.2, Feb 1985, pp.141-149
	w	Clevenger, L.A., "Study of C49-TiSi2 formation on doped polycrystalline silicon using in situ resistance measurements during annealing", J.Appl.Phys. 76 (12) 15 December 1994, pp.7874-7881
	x	

A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.